
Raman - Spectroscopy



innovations
for high
performance

microelectronics

Technical Parameters

Raman-Spectrometer:
Renishaw inVia Raman Microscope

Measurement geometry:
Backscattering

Measurement range: 100 cm⁻¹ - 3200 cm⁻¹

Excitation wavelength:
UV: 325 nm
Visible: 532 nm, 633 nm

Lateral resolution: minimum spot size:
0.6 μm

Scanning and Mapping:
Minimum step: 0.1 μm
Scan range: 30 x 30 mm²

Temperature range: -196°C – 200°C



Application areas

- Thin layer composition (Si, Ge, C)
- Characterization of intrinsic stress
- Quality of Graphene thin layers
- Defect analysis

Contact person

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